VBEQ = 0.691 V

$$A_{V} = -(1 \times 10^{-3})(6.8 \times 10^{3})$$

$$.025$$

d) Drive QPt to eage of saturation VCE = 0.3V what is the change in UBE to $i_{d} = 10 - 0.3 = 1.43 \text{ mA}$ 6.8VBE2-VBE; = VT In (id2) $\Delta V_{BE} = (0.025) ln \left(\frac{1.43}{1} \right)$ $\Delta V_{BE} = 8.94 mV$

Example 2

NPN transistor

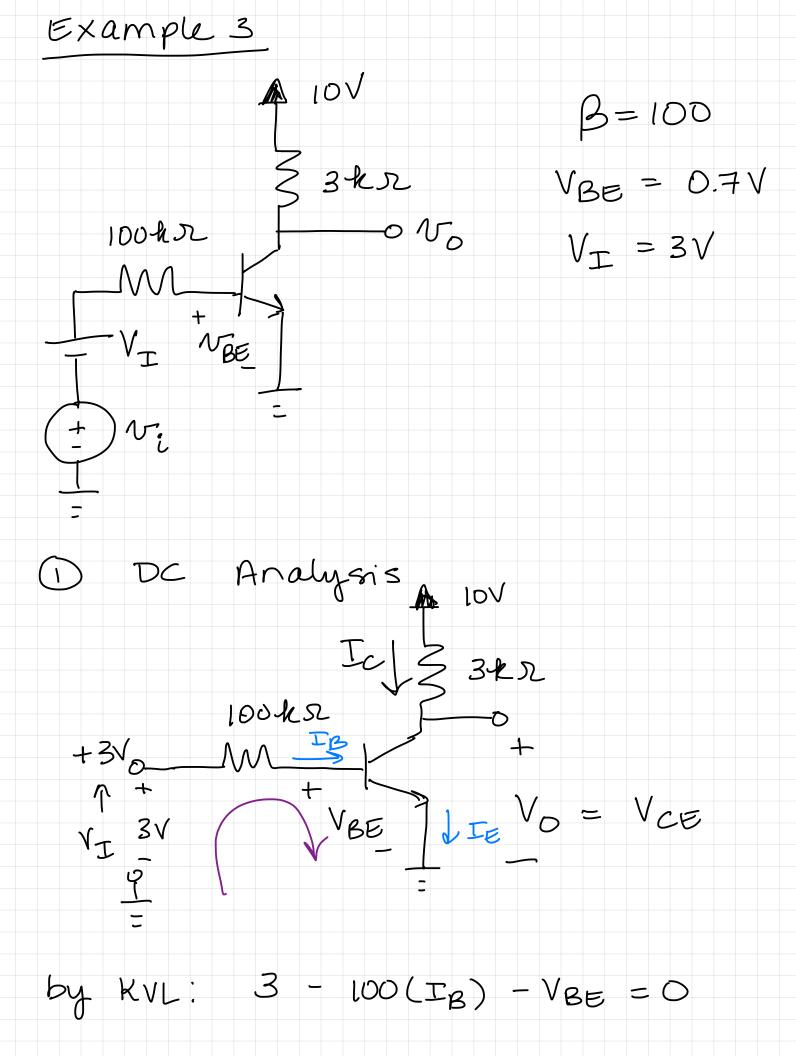
gm, $\Gamma \pi$, re at

Q point $V_T = 25mV$

gm = Icq = ImA = HOmA $VT = .025 \times 10^{-3}$

$$\Gamma_{TT} = \frac{B}{gm} = \frac{100}{40 \, \text{mA/y}} = 2.5 \, \text{RSL}$$

re =
$$\frac{r_{\pi}}{(1+\beta)}$$
 = $\frac{24.75}{1+\beta}$
 $\beta \rightarrow larger$ $\beta+1 \approx \beta$
 $\alpha \approx 1$



$$T_{B} = \frac{3 - 0.7}{100} = 0.023 \, \text{mA}$$

$$T_{C} = \beta \, T_{B} = 100 \, (.023 \, \text{mA})$$

$$T_{C} = 2.3 \, \text{mA}$$

$$V_{CEQ} = V_{QQ} = 10 - T_{CQ} \, R_{C}$$

2) small signal
$$gm = \frac{\text{Icq}}{\text{V}_{T}} = \frac{2.3}{.025} = \frac{92mA}{\text{V}}$$

$$\Gamma_{TT} = \frac{\beta}{3m} = \frac{100}{92 \, \text{mA/V}} = 1.09 \, \text{ks}$$

.025

 \sim

<u>vo</u> = -2.98 V/V